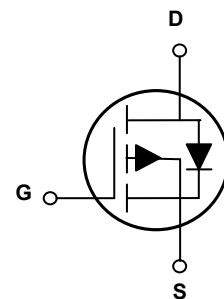
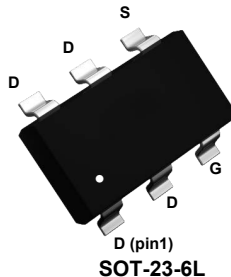


### Main Product Characteristics

$BV_{DSS}$	-20V
$R_{DS(ON)}$	35mΩ (Max.)
$I_D$	-5A



Schematic Diagram

### Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



### Description

The SSF2429 utilizes the latest techniques to achieve ultra high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in battery protection, load switch, power management and a wide variety of other applications.

### Absolute Maximum Ratings ( $T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current-Continuous <sup>1</sup>	$I_D$	-5	A
Drain Current-Pulsed <sup>1</sup>	$I_{DM}$	-20	A
Maximum Power Dissipation	$P_D$	1.4	W
Thermal Resistance Junction-to-Ambient <sup>2</sup>	$R_{\theta JA}$	90	$^{\circ}\text{C}/\text{W}$
Operating Junction Temperature Range	$T_J$	-55 To +150	$^{\circ}\text{C}$
Storage Temperature Range	$T_{STG}$	-55 To +150	$^{\circ}\text{C}$

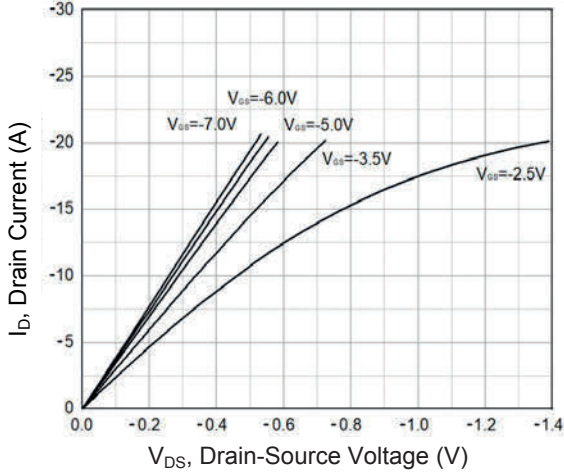
**Electrical Characteristics** ( $T_A=25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	-20	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-20V, V_{GS}=0V$	-	-	-1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
Gate Threshold Voltage <sup>3</sup>	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	-0.5	-0.7	-1	V
Drain Static-Source On-Resistance <sup>3</sup>	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-5A$	-	29	35	m $\Omega$
		$V_{GS}=-2.5V, I_D=-3A$	-	37	48	m $\Omega$
Gate Resistance <sup>3</sup>	$R_g$	$V_{DS}=0V, f=1\text{MHz}$	-	14	-	$\Omega$
Forward Transconductance <sup>3</sup>	$g_{FS}$	$V_{DS}=-10V, I_D=-3A$	4	-	-	S
<b>Dynamic and Switching Characteristics</b>						
Input Capacitance <sup>4</sup>	$C_{iss}$	$V_{DS}=-10V, V_{GS}=0V, F=1\text{MHz}$	-	688	-	pF
Output Capacitance <sup>4</sup>	$C_{oss}$		-	124	-	
Reverse Transfer Capacitance <sup>4</sup>	$C_{rss}$		-	115	-	
Turn-On Delay Time <sup>4</sup>	$t_{d(on)}$	$V_{DD}=-10V, R_{GEN}=6\Omega, V_{GS}=-4.5V, I_D=-1A$	-	5.8	-	nS
Rise Time <sup>4</sup>	$t_r$		-	2.2	-	
Turn-Off Delay Time <sup>4</sup>	$t_{d(off)}$		-	95	-	
Fall Time <sup>4</sup>	$t_f$		-	45	-	
Total Gate Charge <sup>4</sup>	$Q_g$	$V_{DS}=-10V, I_D=-4.5A, V_{GS}=-5V$	-	17.4	-	nC
Gate-Source Charge <sup>4</sup>	$Q_{gs}$		-	1.9	-	
Gate-Drain Charge <sup>4</sup>	$Q_{gd}$		-	2.5	-	
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Diode Forward Voltage <sup>3</sup>	$V_{SD}$	$V_{GS}=0V, I_S=-1.3A$	-	-0.65	-1.3	V
Reverse Recovery Time	$T_{rr}$	$V_R=-10V, I_D=-4.5A, di/dt=100A/\mu s$	-	9.35	-	nS
Reverse Recovery Charge	$Q_{rr}$		-	1.87	-	nC

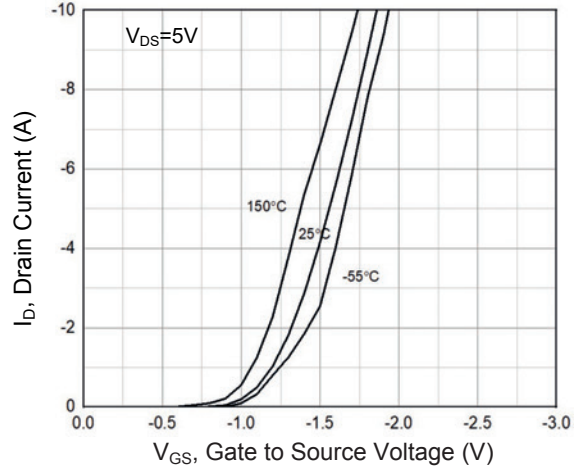
Notes:

1. Repetitive rating: pulse width limited by maximum junction temperature.
2. Surface mounted on 1in<sup>2</sup> FR4 Board,  $t \leq 10$  sec.
3. Pulse test: pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production testing.

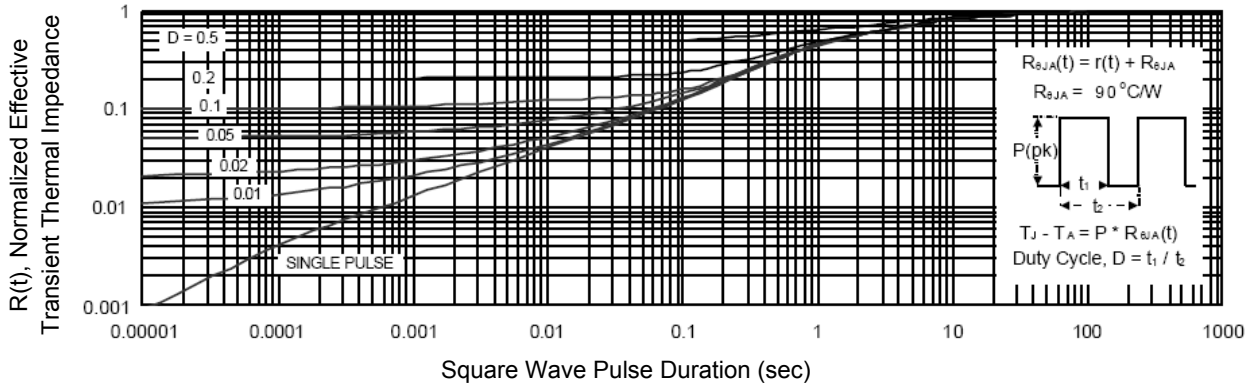
**Typical Electrical and Thermal Characteristic Curves**



**Figure 1. Output Characteristics**

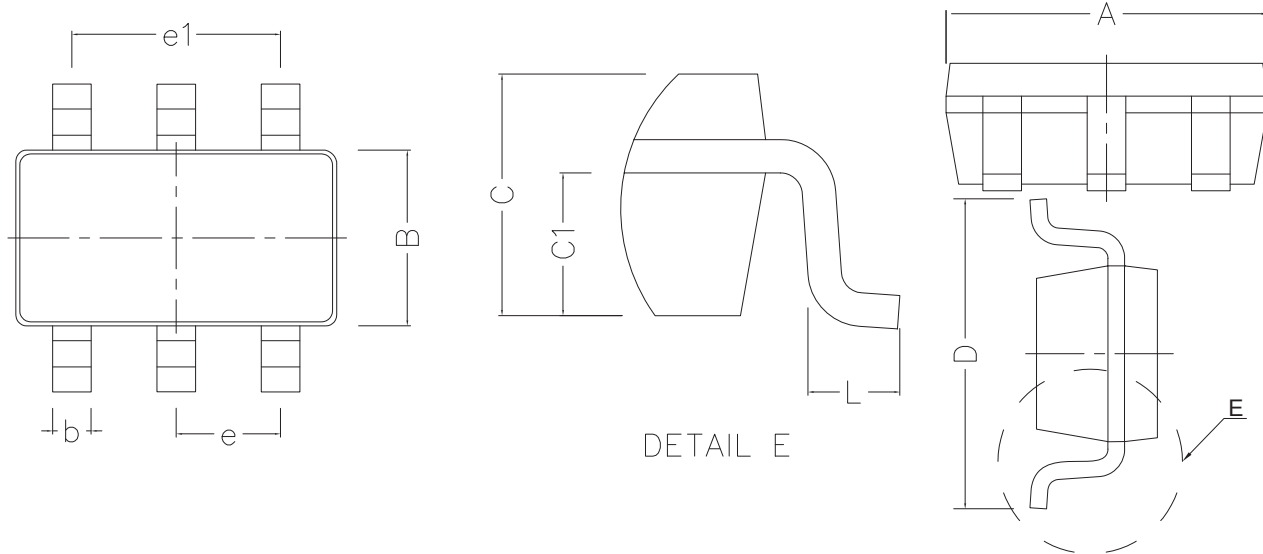


**Figure 2. Transfer Characteristics**



**Figure 3. Normalized Maximum Transient Thermal Impedance**

**Package Outline Dimensions (SOT-23-6L)**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.82	3.02	0.111	0.119
B	1.50	1.70	0.059	0.067
C	1.05	1.15	0.041	0.045
C1	0.60	0.70	0.024	0.028
D	2.65	2.95	0.104	0.116
L	0.30	0.60	0.012	0.024
b	0.28	0.42	0.011	0.017
e	0.95 TYP		0.037 TYP	
e1	1.90 TYP		0.075 TYP	

**Order Information**

Device	Package	Marking	Carrier	Quantity
SSF2429	SOT-23-6L	2429	Tape & Reel	3,000 pcs / 7" Reel

For more information, please contact us at: [inquiry@goodarksemi.com](mailto:inquiry@goodarksemi.com)